Product data sheet

1. General description

Enhanced ultrafast power diode in a SOD59 (2-lead TO-220AC) plastic package.

2. Features and benefits

- · High thermal cycling performance
- Low thermal resistance
- · Low on-state losses
- · Soft recovery characteristic

3. Applications

- Dual Mode (DCM and CCM) PFC
- · Power Factor Correction (PFC) for Interleaved Topology

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit	
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage		600			V	
$I_{F(AV)}$	average forward current	$δ$ = 0.5; square-wave pulse; $T_{mb} \le 115$ °C; Fig. 1; Fig. 2	9			А	
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _{mb} ≤ 115 °C; square-wave pulse	18			А	
I _{FSM} non-repetitive peak forward current		t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 3	91			А	
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	100		Α		
Symbol	Parameter	Conditions	Min Typ Max		Max	Unit	
Static ch	aracteristics						
V _F	forward voltage	I _F = 8 A; T _j = 25 °C; <u>Fig. 5</u>		-	1.45	1.9	V
		I _F = 8 A; T _j = 150 °C; <u>Fig. 5</u>		-	1.25	1.7	V
Dynamic	characteristics				,		
t _{rr}	reverse recovery time	$I_F = 10 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 6$		-	17.5	35	ns

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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode	mb	
2	А	anode		K — A 001aaa020
mb	mb	mounting base; cathode	1 2 TO-220AC (SOD59)	001aaa020

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BYV29F-600	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59		

7. Marking

Table 4. Marking codes

Type number	Marking codes
BYV29F-600	BYV29F-600

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		600	V
V_{RWM}	crest working reverse voltage		600	V
V_R	reverse voltage	DC	600	V
I _{F(AV)}	average forward current	$δ$ = 0.5; square-wave pulse; $T_{mb} \le 115$ °C; Fig. 1; Fig. 2	9	А
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _{mb} ≤ 115 °C; square-wave pulse	18	А
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 3	91	А
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	100	А
T _{stg}	storage temperature		-40 to 150	°C
T _j	junction temperature		150	°C

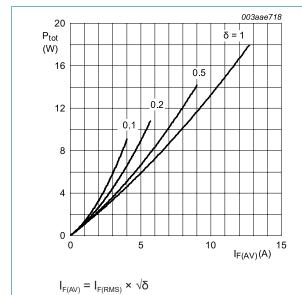


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

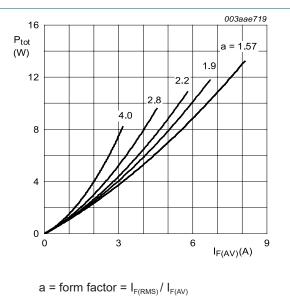


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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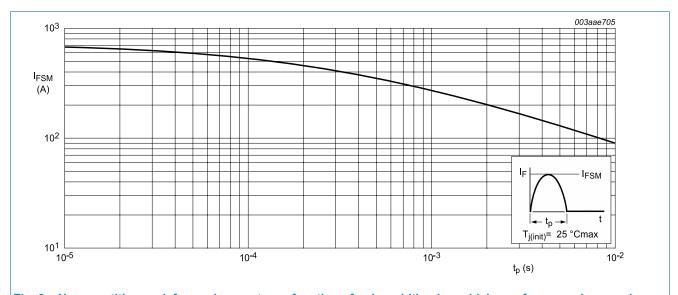


Fig. 3. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig 4	-	-	2.5	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

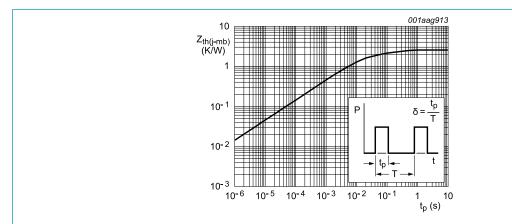


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse width

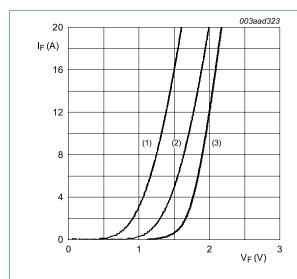
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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics				'	
V_{F}	forward voltage	I _F = 8A; T _j = 25 °C; <u>Fig. 5</u>	-	1.45	1.9	V
		I _F = 8A; T _j = 150 °C; <u>Fig. 5</u>	-	1.25	1.7	V
I _R	reverse current	V _R = 600 V; T _j = 100°C	-	-	1.5	mA
		V _R = 600 V; T _j = 25 °C	-	-	50	μA
Dynamic	characteristics		'	,		
Q _r	recovered charge	$I_F = 1 \text{ A;V}_R = 30 \text{ V; } dI_F/dt = 100 \text{ A/}\mu\text{s}$	-	13	-	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A; } V_R = 30 \text{ V; } dI_F/dt = 100 \text{ A/}\mu\text{s;}$ $T_j = 25 \text{ °C; } \frac{\text{Fig. 6}}{}$	-	17.5	35	ns
I _{RM}	peak reverse recovery current	$I_F = 1 \text{ A}$; $V_R = 30\text{V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; Fig. 6	-	1.5	-	А
V_{FR}	forward recovery voltage	$I_F = 1 \text{ A}; dI_F/dt = 100 \text{ A/}\mu\text{s}; Fig. 7$	-	3.2	-	V



(1) T_j = 150 °C; typical values

(2) T_i = 150 °C; maximum values

(3) T_j = 25 °C; maximum values

Fig. 5. Forward current as a function of forward voltage

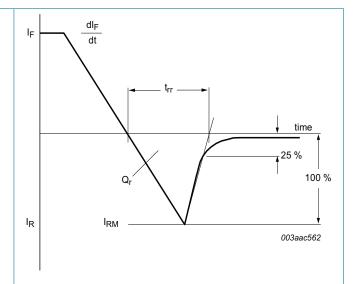
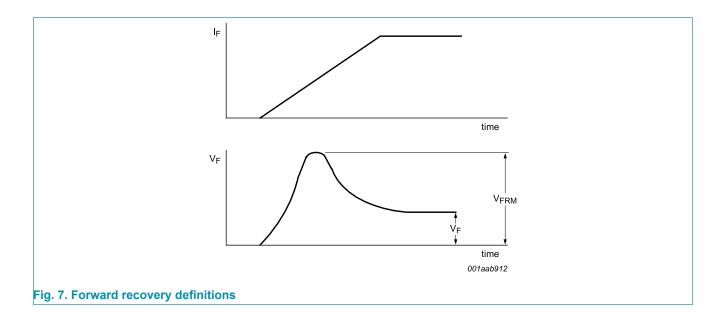
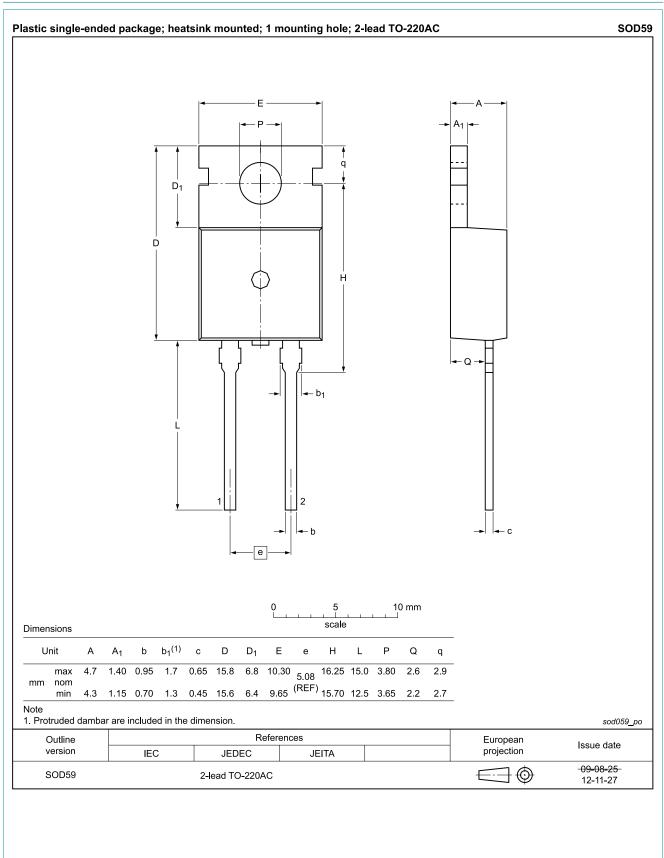


Fig. 6. Reverse recovery definitions; ramp recovery

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11. Package outline



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12. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BYV29F-600 v.3	20180228	Product data sheet	-	BYV29F-600 v.2
Modifications: Change from NXP version to WeEn version				
BYV29F-600 v.2	20110307	Product data sheet	-	BYV29F-600 v.1
Modifications:	Various changes to content.			
BYV29F-600 v.1	20100907	Product data sheet	-	-

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13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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